

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1907	(372/46).CCLS.	USPAT; USOCR	OR	OFF	2005/03/03 08:08
S2	608	S1 and ridge	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 14:46
S3	311	S2 and gap	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 15:26
S6	169	S3 and cleav\$3	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 15:26
S7	163	S6 and etch\$3	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 15:27
S8	84	S7 and current and blocking	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 15:28
S9	75	S7 and current adj blocking	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 16:30
S10	297	S3 and etch\$3	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 15:59
S11	147	S10 and current adj blocking	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 16:28
S12	262	S1 and ridge and current adj blocking	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 16:28
S13	162	S12 and (gap or space)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/28 16:45
S14	2317	(372/45).CCLS.	USPAT; USOCR	OR	OFF	2005/02/28 16:45
S15	2321	(372/45).CCLS.	USPAT; USOCR	OR	OFF	2005/03/01 08:32
S16	265	S15 and ridge and current adj blocking	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 08:32
S17	1	("6025207").PN.	USPAT; USOCR	OR	OFF	2005/03/01 10:57
S18	52229	(semiconductor with laser)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 10:59

S19	3374	S18 and ridge	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 10:59
S20	864	S19 and (current with block\$3)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:00
S21	566	S20 and (gap or break or space or seperation)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:04
S22	558	S21 and substrate	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:05
S23	536	S22 and clad\$4	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:06
S24	339	S23 and conductivity	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:14
S25	303	S23 and cleav\$4	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:16
S26	182	S25 and buried	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 11:59
S27	49	(semiconductor with laser) and ridge and (current with block\$3) and (gap or break or space or seperation)	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/01 12:13
S28	0	sang adj bok adj yun	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 12:15
S29	9	sang and bok and yun	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 12:18
S30	7	sang and bok and yun	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/01 12:19
S31	411	sang and yun	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 12:19
S32	44	S31 and laser	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 12:19
S33	410	semiconductor and laser and cleaving and defect	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/01 12:49
S35	211	S33 and etch\$3	USPAT	OR	OFF	2005/03/01 12:49
S36	45	S34 and ridge	USPAT	OR	OFF	2005/03/01 12:57

S37	35	S35 and wet and dry	USPAT	OR	OFF	2005/03/01 12:57
S39	31	(US-20040165632-\$ or US-20040262259-\$).did. or (US-4745611-\$ or US-4805184-\$ or US-4964135-\$ or US-5020067-\$ or US-5045500-\$ or US-5113405-\$ or US-5469457-\$ or US-5556804-\$ or US-5604764-\$ or US-5764669-\$ or US-5781577-\$ or US-5815522-\$ or US-5825797-\$ or US-5920586-\$ or US-6118800-\$ or US-6238943-\$ or US-6285695-\$ or US-6456640-\$ or US-6556605-\$ or US-6647044-\$ or US-6670211-\$ or US-6671301-\$ or US-6697404-\$ or US-6798808-\$ or US-6829271-\$ or US-6836498-\$).did. or (US-6855570-\$ or US-6856636-\$).did. or (JP-2001094207-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2005/03/02 11:12
S40	5	("4371966" "4849372" "4916709" "4961197" "4964135").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/02 15:07
S41	5	("4371966" "4849372" "4916709" "4961197" "4964135").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/02 15:07
S42	4	("5020067").URPN.	USPAT	OR	ON	2005/03/02 15:24
S43	17341	("372").CLAS.	USPAT; USOCR	OR	OFF	2005/03/03 08:09
S44	1547	S43 and ridge	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 09:02
S45	79	S44 and astigmatism	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 08:10
S46	158	S44 and defect and cleav\$3	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 09:30
S47	278	S44 and defect and etch\$3	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 09:31
S48	48	S47 and wet and dry	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 09:57

S49	53	S47 and (wet or chemical) with (dry or plasma)	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 09:58
S53	535	((semiconductor with laser) and ridge and defect and etch\$3) not "372".clas.	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 12:17
S54	163	S53 and ((wet or chemical) with (dry or plasma))	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/03/03 12:18